

Amendments to the Claims

Claim 1-53 (cancelled).

Claim 54 (new): A method for removing organic materials comprising removing at least a portion of an organic-material-comprising layer from a semiconductive substrate surface with a pad and a fluid, the fluid being substantially unreactive with the surface and comprising less than or equal to about 0.1 weight percent particles at an initiation of the removing.

Claim 55 (new): The method of claim 54 wherein the organic-material-comprising layer comprises one or more of photoresist, non-photosensitive resist, and polyimide.

Claim 56 (new): The method of claim 54 wherein a pH of the fluid is from about 8 to about 12.

Claim 57 (new): The method of claim 54 wherein the fluid comprises one or both of ammonia and TMAH.

Claim 58 (new): The method of claim 54 wherein the fluid comprises water.

Claim 59 (new): The method of claim 54 wherein the surface comprises a conductive material.

Claim 60 (new): The method of claim 59 wherein the conductive material comprises one or more of platinum, iridium, ruthenium, and tantalum.

Claim 61 (new): The method of claim 54 wherein the surface comprises a barrier material.

Claim 62 (new): The method of claim 61 wherein the barrier material comprises one or both of tantalum silicon nitride and tantalum nitride.

Claim 63 (new): The method of claim 54 wherein the pad comprises polyurethane.

Claim 64 (new): The method of claim 54 wherein at least some of the particles comprise silica.

Claim 65 (new): The method of claim 54 wherein the surface comprises at least two layers, a first conductive layer of the two layers comprising N and Si, and a second conductive layer of the two layers comprising N.

Claim 66 (new): A method for forming a capacitor structure comprising:

providing a substrate comprising an insulative layer over a semiconductive layer, the insulative layer having a recess therein, the recess having a periphery comprising a bottom and sidewalls, wherein the bottom comprises an upper surface of the semiconductive layer;

forming a first conductive-material-comprising layer over the substrate, the first conductive-material-comprising layer lining the bottom and the sidewalls to partially fill the recess and extending laterally outward from the recess over an upper surface of the substrate;

filling the partially filled recess with an organic material, the filling forming an organic material layer over an upper surface of the first conductive-material-comprising layer;

removing at least a portion of the organic material with a pad and an organic-material-removing fluid, wherein the organic-material-removing fluid is substantially unreactive with the first conductive-material-comprising layer and comprises less than or equal to 0.1 weight percent particles at an initiation of the removing;

stopping the removing when substantially all of an upper surface of the laterally extending first conductive-material-comprising layer is exposed;

forming a dielectric layer over the first conductive-material-comprising layer; and

forming a second conductive-material-comprising layer over the dielectric layer.

Claim 67 (new): The method of claim 66 wherein the organic-material-removing fluid comprises about 0 weight percent particles at an initiation of the removing.

Claim 68 (new): The method of claim 66 wherein the organic material comprises one or more of photoresist, non-photosensitive resist and polyimide.

Claim 69 (new): The method of claim 66 further comprising baking the organic material prior to the removing.

Claim 70 (new): The method of claim 66 wherein, after stopping the removing, a plug of the organic material remains in the recess and, prior to forming the dielectric layer, removing the plug to expose the first conductive-material-comprising layer lining the bottom and the sidewalls.

Claim 71 (new): The method of claim 70 wherein the removing the plug comprises a chemical or plasma process.

Claim 72 (new): The method of claim 66 wherein the first conductive-material-comprising layer comprises one or more of platinum, iridium, ruthenium, and tantalum.

Claim 73 (new): The method of claim 66 wherein the first conductive-material-comprising layer comprises one or both of tantalum silicon nitride and tantalum nitride.

Claim 74 (new): A material removal method comprising

providing a substrate supporting a conductive-material-comprising layer, the conductive-material-comprising layer having an organic-material-comprising layer thereover;

selectively removing at least a portion of the organic-material-comprising layer with a first polishing process utilizing a first liquid to thereby expose at least a portion of an upper surface of the conductive-material-comprising layer, wherein the first liquid is substantially unreactive with the conductive-material-comprising layer and comprises less than or equal to 0.1 weight percent particles at an initiation of the removing; and

removing at least a portion of the conductive-material-comprising layer with a second polishing process utilizing a second liquid.

Claim 75 (new): The method of claim 74 wherein the conductive-material-comprising layer comprises one or more of platinum, iridium, ruthenium, and tantalum.

Claim 76 (new): The method of claim 74 wherein the organic-material-comprising layer comprises one or more of photoresist, non-photosensitive resist and polyimide.

Claim 77 (new): The method of claim 74 wherein the first polishing process comprises removing at least a portion of the organic-material-comprising layer with a chemical mechanical polishing pad and the first liquid.

Claim 78 (new): The method of claim 77 wherein the second polishing process comprises removing at least a portion of the conductive-material-comprising layer with the chemical mechanical polishing pad and the second liquid.

Claim 79 (new): The method of claim 74 wherein the first liquid comprises water.

Claim 80 (new): The method of claim 74 wherein the first liquid comprises one or both of ammonia and TMAH.

Claim 81 (new): The method of claim 74 wherein the second liquid comprises less than or equal to approximately 0.1 weight percent particles at an initiation of the removing of the conductive-material-comprising layer.

Claim 82 (new): The method of claim 74 wherein the second liquid comprises particles.

Claim 83 (new): The method of claim 74 wherein a composition of the second liquid is different than a composition of the first liquid.

Claim 84 (new): The method of claim 74 wherein the second liquid is reactive with the conductive-material-comprising layer.

Claim 85 (new): The method of claim 74 wherein the conductive-material-comprising layer comprises a barrier material.

Claim 86 (new): The method of claim 77 wherein the barrier material comprises one or both of tantalum silicon nitride and tantalum nitride.